Docket No.: Z&PINFN10455

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : JOSEF BOECK

Filed : CONCURRENTLY HEREWITH

Title : PROCESS FOR PRODUCING TWO DIFFERENTLY DOPED ADJACENT REGIONS IN AN INTEGRATED SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

S i r :

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent 3,974,516 (Steinmaier), dated August 10, 1976;

U.S. Patent 5,213,988 (Yamauchi et al.), dated May 25, 1993;

U.S. Patent 5,747,374 (Jeon), dated May 5, 1998;

Patent Abstracts of Japan 58 155 764 (Yasuhisa), dated September 16, 1983;

Patent Abstracts of Japan 59 006 574 (Tetsuo), dated January 13, 1984;

Kameyama, S. et al.: "Base Link-Up Process Technology for Self-Aligned Double Diffusion Bipolar Transistors", IEEE, 1987, pp. 27-30;

Nakamae, M.: "Recent Progress and Future Prospect for VLSI Si Biopolar Transistors", IEEE, 1987, pp. 5-6;

Chen, T et al..: "An Advanced Bipolar Transistor with Self-aligned Ion-implanted Base and W/poly Emitter", IEEE, 1987, pp. 31-33;

Yamaguchi, T. et al.: "Process and Device Performance of a High-Speed Double Poly-Si Bipolar Technology Using Borosenic-Poly Process with Coupling-Base Implant", IEEE, Vol. 35, No. 8, August 1988, pp. 1247-1256;

Sugiyama, M. et al.: "A40GHz f_T Si Bipolar Transistor LSI Technology", IEEE, 1989, pp. 9.1.1-9.1.4;

Van der Velden, J. et al.: "Basic: An Advanced High-Peformance Bipolar Process", IEEE, 1989, pp. 9.4.1-9.4.4;

Shiba, T. et al.: "Base Peripheral Effects on High Performance Self-Aligned Bipolar Devices (SICOS)", Scripta Technica, Inc., 1990, pp. 100-105;

Hayden, J. D. et al.: "A New Technique for Forming a Shallow Link Base in a Double Polysilicon Bipolar Transistor", IEEE, 1994, pp. 63-68;

Park, J. et al.: "Ultrashallow p^+/n Junction Formation by 0.5-1 keV Ion Implantation", Japanese Journal of Applied Physics, Vol. 37, No. 11B, 1998, pp. L1376-L1378;

International Search Report, dated July 20, 1999.

Respectfully submitted,

For Applicant

Date: January 22, 2002

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